

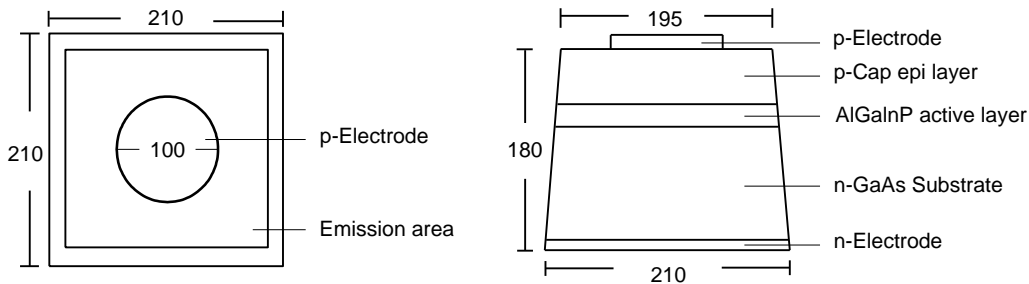
■ **Features :**

- MOVPE Epi Wafer
- Suitable for New Creative Products

■ **Typical Applications :**

- Automotive Signal Lamps: Center High Mount Stop Lights
- Traffic Signs
- Semi-Outdoor Panels
- Night Lights/ LED Electric Torch

■ **Outline Dimensions : (Unit: um)**



■ **Physical Structure :**

Chip dimension	Chip size	210 um x 210 um
	Thickness	180 um
	Emission area	195 um
	Bonding pad	100 um
Electrode	Top: P (anode)	Aluminum (Gold optional)
	Backside: N (cathode)	Gold alloy
Surface condition	Not frosted	

■ **Electro-Optical Characteristics : (Ta = 25°C)**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 20 \text{ mA}$	-	2.00	2.40	V
Reverse Voltage	V_R	$I_R = 10 \text{ uA}$	5	-	-	V
Wavelength	λ_p	$I_F = 20 \text{ mA}$	-	632	-	nm
	λ_D		619	624	629	
Spectral width at half height	$\Delta \lambda$	$I_F = 20 \text{ mA}$	-	20	-	nm
Luminous Intensity	I_v	$I_F = 20 \text{ mA}$	100	-	-	mcd
			120	-	-	
			150	-	-	
			180	-	-	

■ Typical Electro-Optical Characteristics Curve:

Fig 1. Forward Current vs. Forward Voltage

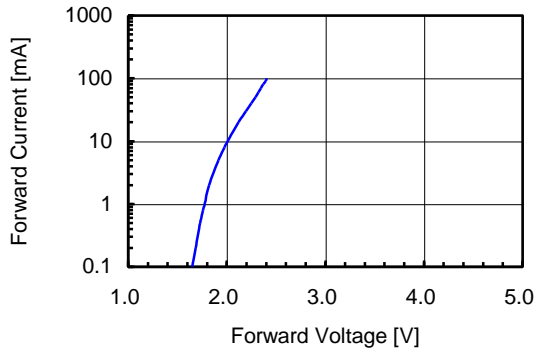


Fig 2. Relative Intensity vs. Forward Current

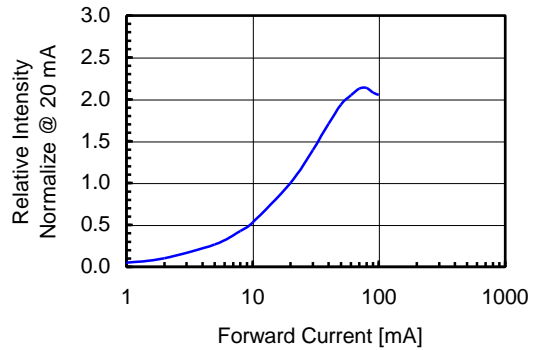


Fig 3. Forward Voltage vs. Temperature

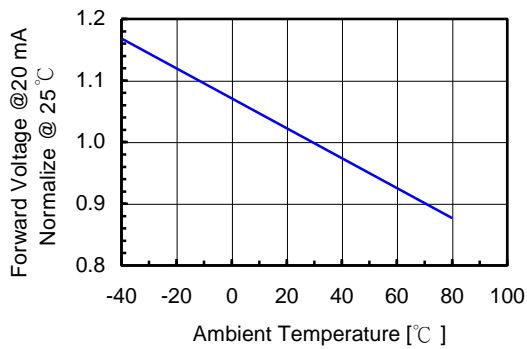


Fig 4. Relative Intensity vs. Temperature

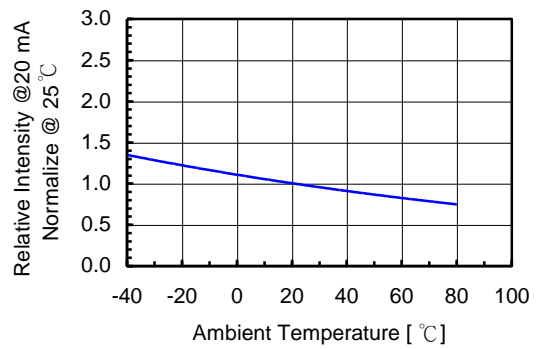


Fig 5. Relative Intensity vs. Wavelength

